
A Hybrid III-V-on-silicon micro-laser with Resonant Cavity Mirrors

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Abstract: A novel approach is presented to realise compact III-V-on-silicon micro-lasers. The concept relies on resonant mirrors in which the close interaction between a III-V waveguide and an underlying silicon cavity provides high, narrow-band reflection back into the III-V waveguide. Combining two such mirrors with a III-V waveguide in between leads to a resonant mirror laser. The properties of the resonant mirror are studied for a variety of device parameters. Using this information, the properties of the resulting laser, such as threshold power and side-mode suppression ratio are investigated. These calculations correspond well to proof-of-concept experimental results.

Index Terms: silicon photonics, heterogeneous III-V integration, lasers, bonding, micro-lasers, micro-cavity

1. Introduction

Over the last decade, silicon has grown to be one of the most important material systems available for integrated photonic components and circuits. Combining the mature fabrication technology inherited from CMOS electronics with the high refractive index contrast between the silicon waveguide core and its surrounding cladding allows for unprecedented miniaturization and integration of passive optical components as well as high speed modulators and detectors. Unfortunately, silicon has an indirect bandgap, making it unsuitable as a laser gain material. Over the years, a number of approaches have been proposed to enable laser sources on silicon-based nanophotonic platforms. Examples are epitaxial growth of a direct-bandgap III-V material on top of the silicon substrate [1], exploiting non-linear photon interaction in the silicon itself [2] or using strained and doped germanium on top of the silicon layer as a laser gain medium [3]. But the most performant approach to date is the so-called hybrid III-V on silicon integration. A III-V semiconductor die with an epitaxial structure grown on top, is bonded upside-down onto a patterned silicon-on-insulator (SOI) die, using either molecular or adhesive bonding [4]. After the III-V substrate is removed, the remaining III-V film (thickness from below 100 nm to a few μm) is patterned using a series of lithography and etching steps. Finally metal contacts are added to obtain the desired laser structure.

A number of hybrid laser types have been presented over the last years. DFB- and DBR-lasers were demonstrated using both molecular [5] and adhesive [6] bonding. In both cases the optical mode is mainly confined to the passive silicon layer but its evanescent tail reaches into the III-V overlay where it experiences optical gain. This approach results in relatively large devices ($> 400 \mu\text{m}$) and consequently a high threshold current ($> 20 \text{ mA}$). However, reducing the laser threshold current to shrink the overall power consumption is of paramount importance in many applications. One way to reduce the threshold current is to scale down the physical size of the laser. Examples of such so-called micro-lasers are III-V micro-disk lasers [7], linear III-V photonic-

crystal cavity lasers [8] and photonic-crystal mirror VCSELs [9]. The threshold pump power for these micro-lasers is on the order of 1 mW or less. Electrically injected micro-disk lasers have been demonstrated but the disk cavity supporting whispering gallery modes lacks an inherent wavelength selection mechanism to prevent mode-hopping and multi-mode lasing. The linear III-V photonic crystal cavity laser and photonic-crystal mirror VCSEL laser are inherent single-mode laser cavities but electrical injection has not yet been demonstrated. In this work we propose a novel design for heterogeneously integrated III-V on silicon micro-lasers that promises to enable small-footprint, single-mode lasers with precise wavelength control and a low laser-threshold. In the first part of this paper we will introduce the general concept of the proposed laser, that revolves around the concept of resonant cavity mirrors. We will also provide an in-depth discussion of a number of mirror designs and the influence of the different parameters on the reflectivity spectrum. In the second part we will discuss how this mirror fits in the overall laser design and estimate the expected laser characteristics.

Resonant Cavity Mirror Lasers

The general layout of the proposed laser concept is depicted in figure 1. Like any other laser, this design consists of two mirror sections with an active gain section in between. The gain section consists of a III-V waveguide with no silicon waveguide underneath (*Gain Section* in figure 1). In other words, the optical mode traveling through the gain section is fully confined to the III-V waveguide. This way the overlap between the optical mode and the active layer in the gain section is optimized. In each mirror section a silicon grating cavity lies underneath the III-V waveguide. This can be a finite grating that supports a number of band-edge resonances or a grating with a quarter-wave shift that supports a localized defect resonance. When the light propagating in the III-V waveguide reaches the section with the silicon cavity underneath (**1** in figure 1), a small fraction couples (**2**) to the silicon resonator. If the wavelength of the light is close to the silicon cavity resonance wavelength, power will start to build up in this cavity (**3**). If the energy contained in the silicon cavity is high enough, a significant amount of light will couple back into the III-V waveguide. The light coupling back co-directionally to the III-V waveguide (**4**) will interfere destructively with the light that didn't couple to the silicon cavity, yielding, in the ideal case, no transmission through the III-V waveguide (**7**). The light that couples back into the III-V waveguide counter-directionally to the incident light (**5**) will provide the feedback necessary for laser operation. Since this is a resonant phenomenon, the reflection bandwidth of this mirror will be narrow, which is useful for single mode operation. Although the size of the mirror structure largely depends on the actual cavity implementation, we will propose designs where the mirror is shorter than $30\ \mu\text{m}$. This approach to implementing compact, wavelength selective optical feedback also provides an elegant mechanism to couple the generated laser light to an external silicon waveguide. Because light is already present in the silicon cavities, one of these cavities can be engineered to leak a small amount of light into an external silicon waveguide (**6**).

This interplay between a III-V waveguide and a silicon cavity underneath that results in narrow-band reflection back into the III-V waveguide is called a *resonant mirror*. The combination of two such mirrors with a III-V gain section in between is a resonant mirror laser. The laser wavelength is determined by the overlap between the active material's gain spectrum, the narrow reflectivity spectrum of the mirrors and the spectral position of the longitudinal modes in the III-V waveguide. For this type of laser, nearly all important laser parameters, such as lasing wavelength, threshold power and side-mode suppression ratio are to a large extent determined by the reflectivity spectrum of the resonant mirror. This work will therefore first investigate the reflectivity spectrum of different resonant mirror designs using full-vectorial 3D-FDTD simulations. For each design, the influence of the predominant parameters in the system will be explained. Second the calculated spectrum is used to estimate the laser properties such as the threshold power and side-mode suppression ratio.

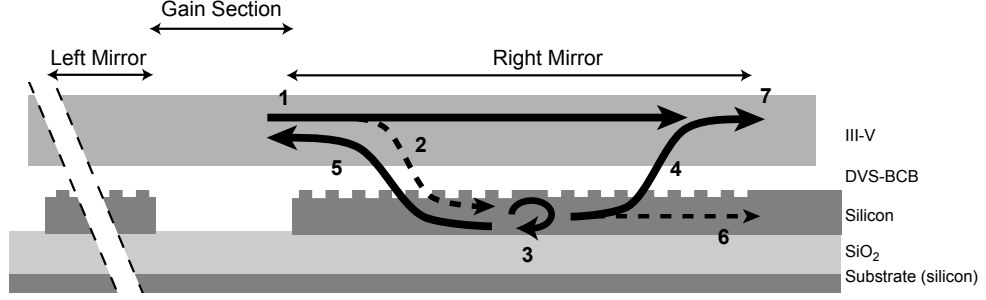


Fig. 1. **Schematic side view of a heterogeneously integrated Si/III-V laser with resonant mirrors.** The different arrows illustrate the operation of the grating cavity as a mirror. The dimensions on this scheme are not to scale, especially the length of the gain section is greatly reduced for the sake of clarity

Technology platform and simulation tools

In this study the silicon waveguide structure is assumed to be fabricated on a standard 220 nm SOI platform: on top of the silicon substrate lies a $2\text{ }\mu\text{m}$ thick silicon oxide layer ($n_{\text{SiO}_2} = 1.45$) that is covered with another 220 nm thick silicon layer ($n_{\text{Si}} = 3.477$). The silicon grating cavities are strip waveguides (220 nm etch) with 70 nm deep etched corrugations. The choice for this particular waveguide structure is motivated by the fact that it can be fabricated in a widespread and mature technological process based on CMOS fabrication processes. Also, many passive optical components with excellent properties have been demonstrated in this technology. To enable close integration of optical functions, the silicon layer of the laser source and the passive silicon components should be fabricated in the same technology. However, the conclusions that will be drawn from the simulations performed in this particular material system can be extended to any other high-index-contrast technology.

The silicon die is covered by a thin layer of divinylsiloxane benzocyclobutene (DVS-BCB - $n_{\text{BCB}} = 1.55$) as this is the material used for adhesive bonding [10]. The III-V layer is 240 nm thick and consists of an 80 nm bulk InGaAsP active layer ($n_{\text{InGaAsP}} = 3.57$) sandwiched between non-intentionally doped InP layers ($n_{\text{InP}} = 3.1649$). The waveguide in the III-V layer is $1.6\text{ }\mu\text{m}$ wide. To simplify the analysis, the III-V waveguide has no electrical contacts. To pump the active region, the structure is illuminated from the top with a pump laser beam. It is possible to pump the active region electrically, for example by using lateral injection as proposed in [11], but this is outside the scope of the present work.

Throughout this paper, we make extensive use of the open-source 3D FDTD package MEEP [12]. Reflection and transmission spectra are calculated by launching a short pulse into the III-V waveguide and measuring the reflected and transmitted power-flux in the same waveguide. Q-factors are extracted using harmonic inversion [13] of the electric-field time-trace inside the cavity after the initial excitation has faded-out. Dispersion diagrams are calculated using the open-source package MPB [14]. TE polarised light is used throughout the paper.

2. Band-edge resonators

Consider the dispersion diagram of a $1.6\text{ }\mu\text{m}$ wide silicon waveguide grating (period = 285 nm , duty cycle 50%) in figure 2a. The figure shows that this particular grating does not support propagating modes between $\lambda = 1492\text{ nm}$ and $\lambda = 1570\text{ nm}$, the so-called photonic band-gap. A direct consequence of this photonic band-gap is the flattening of the dispersion curve near the edges of the gap where $d\omega/dk$ (hence also $d\lambda/dk$) reaches zero at $k = \pi/\Lambda$. Since the group velocity v_g is proportional to $d\omega/dk$, the guided modes near the edge of the band will have a decreased group velocity and are called 'slow-light' modes.

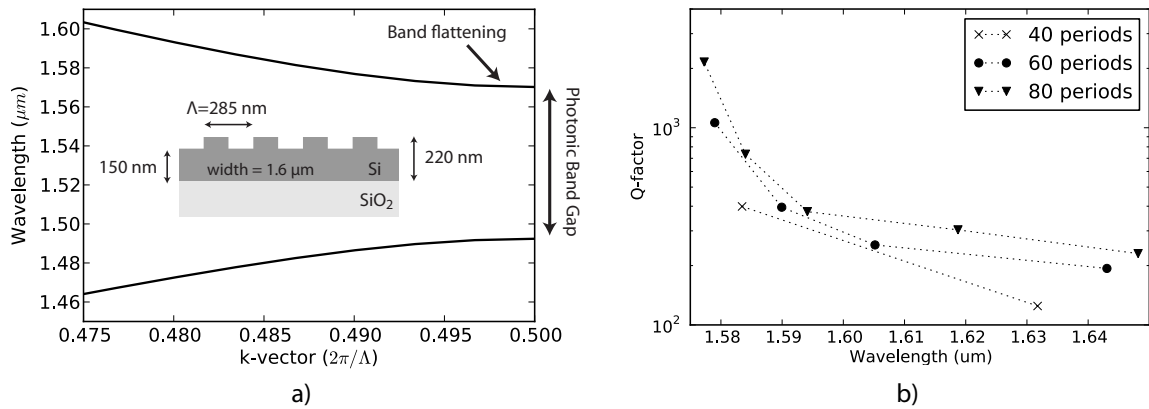


Fig. 2. a) Band diagram for a silicon waveguide grating with dimensions as indicated in the figure. b) Resonance wavelengths (indicated by the scatter points) and corresponding Q-factors for the band-edge resonances in such a waveguide grating. The different curves are for different cavity lengths. The dotted line serves as a guide to the eye to connect the different resonances in the same structure.

In a grating of finite length, the mode experiences reflection at the facets, leading to Fabry-Perot resonances. But due to their low group velocity, it takes the modes near the band-edge a longer time to travel through the cavity, increasing the Q-factor significantly as compared to Fabry-Perot cavities of similar length and facet reflectivity. For a more in-depth theoretical treatment of band-edge resonances, see [15].

2.1. Intrinsic cavity properties

Figure 2b shows the frequencies and corresponding Q-factors for the band-edge resonances of a $1.6 \mu\text{m}$ wide silicon grating cavity. These Q-factors are for the intrinsic grating cavities, so there is a thin layer of BCB on top of the gratings but no III-V waveguide. The grating period is 285 nm (50 % duty cycle). The different curves in figure 2b are for 40, 60 and 80 periods. For such short cavity lengths and in the absence of material absorption, the predominant loss mechanism in this type of cavity that limits the Q-factor is leakage from the grating's end-facets. That explains why the Q-factor is maximum near the band-gap and increases with an increasing number of periods: in both cases it takes the photons a longer time to travel between the facets. As could be expected from a Fabry-Perot like cavity, increasing the number of periods (so increasing the cavity length) will increase the spectral resonance density. On the other hand, the spectral spacing between different resonances is not constant as in a classic Fabry-Perot resonator, but increases as the group velocity increases when going away from the band-edge.

2.2. Band-edge resonators used as resonant mirrors

Figure 3a shows the typical reflection and transmission spectrum of a resonant mirror with a band-edge grating resonator. This spectrum was calculated by launching the fundamental eigenmode into the III-V waveguide (1 in figure 1) and collecting the reflected eigenmode in the same location. The transmission spectrum was also calculated in the III-V waveguide at position 7 in figure 1. In this particular example, the silicon cavity consists of a 60 period grating with a 285 nm pitch. The distance between the top of the silicon waveguide and the bottom of the III-V waveguide (the *bonding layer thickness*) is 300 nm . The silicon waveguide grating is $1.6 \mu\text{m}$ wide and the III-V waveguide is $1.5 \mu\text{m}$ wide. At the resonance wavelength (1577.95 nm) the total reflection back into the III-V waveguide is 81.65 % while only 2 % is transmitted through the III-V waveguide. The reflection bandwidth (FWHM) is 14 nm . Consequently, the Q-factor for the loaded system (silicon cavity + III-V waveguide) is 112.7. This is considerably lower than the silicon cavity's intrinsic

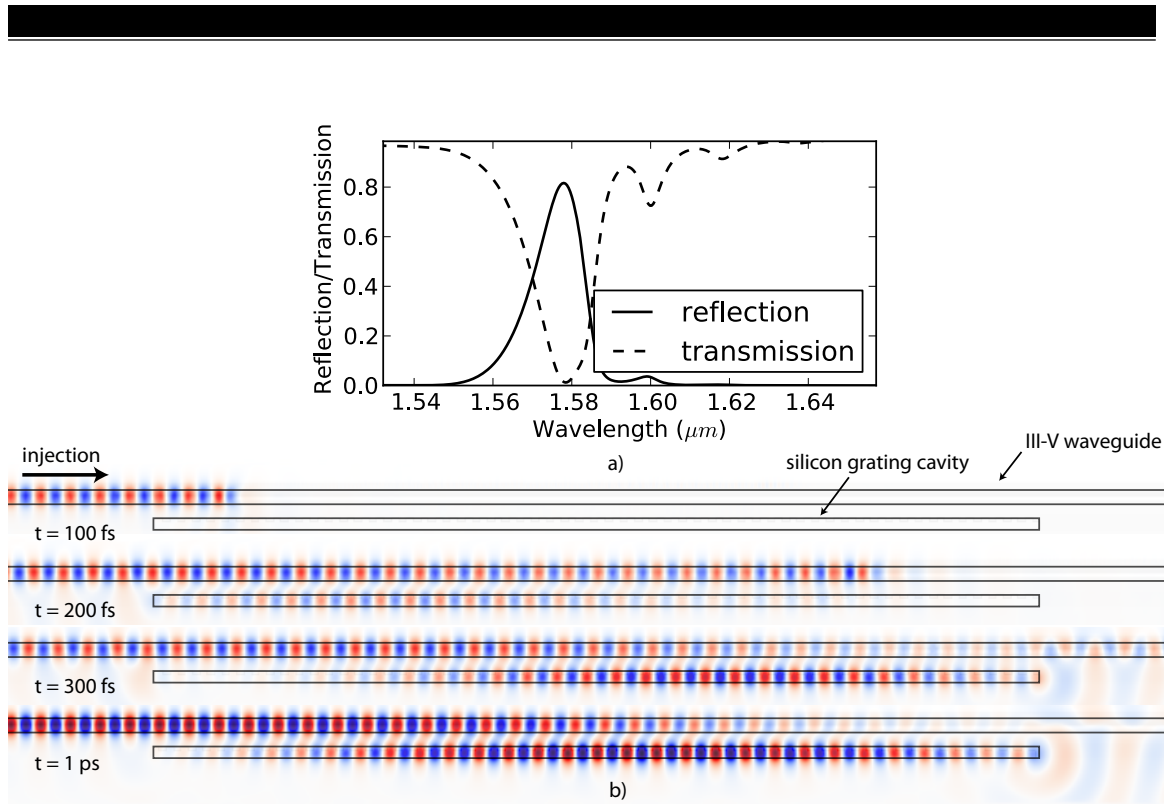


Fig. 3. a) reflection and transmission spectrum of a resonant mirror using a silicon band-edge cavity with 60 periods and a grating pitch of 285 nm. b) Field profiles through a cross-section at different points in time for CW injection (at resonance wavelength) of the same structure.

Q-factor (≈ 1000), meaning that the loss in the silicon cavity is now dominated by coupling to the III-V waveguide.

To gain more insight into the operation of the mirror, figure 3b shows the electric field in a cross-section similar to figure 1 at 4 different points in time. A CW signal ($\lambda = 1578 \text{ nm}$, the mirror's resonance wavelength) is injected into the III-V waveguide ($t = 100 \text{ fs}$). Only a small fraction of the light in the III-V waveguide couples to the silicon cavity ($t = 200 \text{ fs}$) and most of the light propagates through the III-V waveguide ($t = 300 \text{ fs}$). Once the energy in the silicon cavity is sufficiently high ($t = 1 \text{ ps}$), light is reflected back into the III-V waveguide. Consequently light is no longer transmitted through the III-V waveguide. The electric field amplitude in the III-V waveguide is higher at $t = 1 \text{ ps}$ because the forward (incoming) wave and the backward (reflected) wave both propagate through the same waveguide, giving rise to a standing wave. The same figure also clearly shows that most of the light that is not reflected leaks away from the right-hand side of the silicon cavity. This light can be collected by adding a silicon waveguide at the end of the cavity to serve as an output port of the laser.

The most important properties of a resonant mirror based on band-edge resonances, maximum reflectivity and reflection bandwidth, are mainly determined by the quality-factor of the silicon cavity and the degree of coupling between the silicon cavity and the III-V waveguide. These two properties are predominantly controlled by the length of the silicon grating and the bonding layer thickness. The next two paragraphs will elaborate on the influence of these two design parameters.

2.2.1. Influence of grating length

Figure 4a shows the reflection (solid) and transmission (dashed) spectra for three different mirrors. The three mirrors are identical to the structure in the previous paragraph (figure 3a) except for

the number of periods in the silicon grating. When increasing the length of the silicon grating, three things happen. First, the resonance wavelengths of the resonances in the intrinsic cavity shift towards shorter wavelengths as can be seen in figure 2b. Second, the Q-factor of these resonances increases (also on figure 2b). Finally, because the band-edge mode is not localized but spread out along the length of the grating, increasing the number of grating periods will increase the interaction length between the III-V waveguide and the silicon cavity.

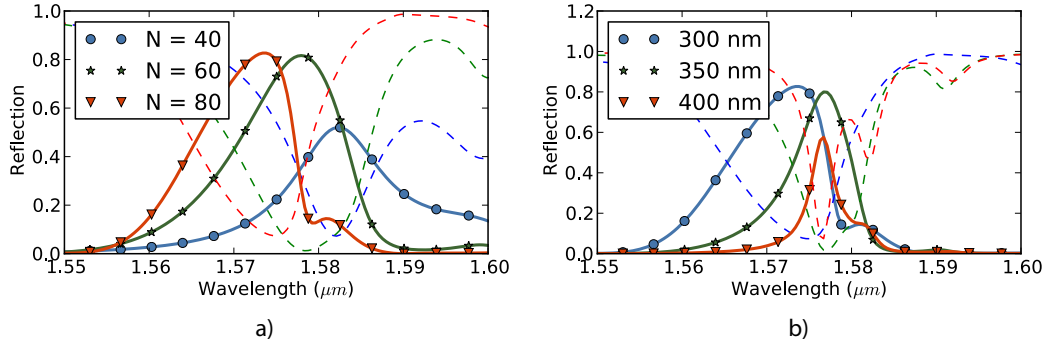


Fig. 4. Influence of the number of periods (a) and BCB thickness (b) on the reflection spectrum of a band-edge resonant mirror. Except for the variable parameter, the structure is identical to the one presented in figure 3. Solid lines are reflection spectra, dashed lines are transmission spectra

These three effects explain the behaviour of the different spectra in figure 4a. The wavelengths of the reflection maxima in figure 4a correspond to the resonance wavelengths in figure 3b. When increasing the grating length from 40 periods to 60 periods, the maximum reflectivity increases from around 50% to 81.6%. This is the result of both the increase in Q-factor and the longer interaction length, increasing the coupling. For 60 periods, the power transmitted through the III-V waveguide is almost zero. This indicates that the cavity is critically coupled to the III-V waveguide. If the number of periods is increased to 80, the maximum reflectivity only slightly increases from 81.6 % to 82.6 %. The amount of power that is transmitted through the III-V waveguide increases to around 10 %. This indicates that the III-V waveguide is no longer critically coupled to the silicon cavity. Even though the reflection is slightly higher, this situation is not desirable because only 10% of the incoming light can be coupled to the silicon output waveguide instead of almost 20% in the case of 60 periods. The reflection bandwidth does not change significantly when varying the number of grating periods.

2.2.2. Influence of bonding layer thickness

Figure 4b shows the reflection and transmission spectra for resonant mirrors with 80 period long silicon gratings and a bonding layer thickness of 300 nm, 350 nm and 400 nm. All other parameters are identical to the structure presented in figure 3. Varying the bonding layer thickness mainly affects the coupling between the III-V waveguide and the silicon cavity. For this particular configuration, the system is critically coupled if the bonding layer thickness is 350 nm (zero transmission through the III-V waveguide).

Similar to the discussion in paragraph 2.2.1, the maximum reflectivity for the over-coupled system is slightly higher than the critically coupled case, but again this configuration is not desirable because 10% of the incident light is lost through the III-V waveguide. Increasing the bonding layer thickness will reduce the coupling between the III-V waveguide and the silicon cavity, in its turn reducing the maximum reflectivity. The FWHM bandwidth of the reflection peak also clearly reduces for increasing bonding layer thickness. The wavelength for peak-reflectivity is weakly dependent on the bonding layer thickness. For a thinner bonding layer thickness, the evanescent

tail of the silicon cavity mode feels the presence of the III-V waveguide on top, slightly changing the resonance wavelength of the combined system.

3. Defect resonators

3.1. Introduction

By adding a defect to the periodic silicon grating, the structure now supports a localized mode within the photonic bandgap. Light in the defect is trapped between two barriers, which can lead to a resonator with higher Q-factors than band-edge resonators of equal length. The inset in figure 5 shows how the defect is introduced by adding a quarter-wave shift to the grating waveguide discussed in section 2.

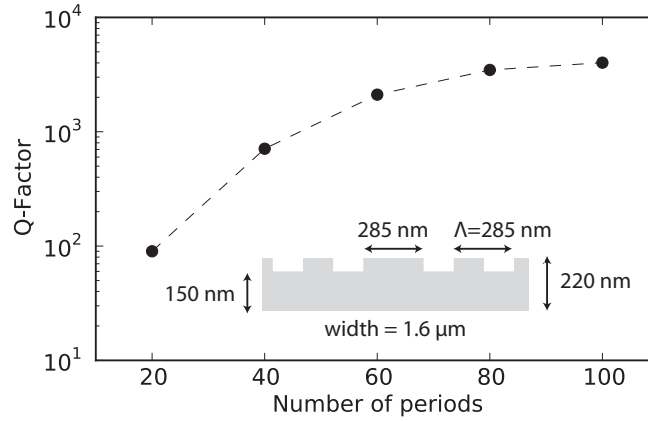


Fig. 5. Q-factor of the intrinsic defect resonators for different cavity lengths. The dimensions of the cavity are as indicated in the figure. The defect is always located in the center of the grating.

3.2. Intrinsic cavity properties

Figure 5 plots the intrinsic cavity Q-factor as a function of the total number of periods of the structure. The defect is always located in the center of the grating (for example: for a total number of 60 periods, the defect is between two gratings of 30 periods each). The resonance wavelength is independent of the number of periods and is 1534 nm in this particular case (285 nm pitch). The Q-factor saturates to a value around 4000 for cavities with 100 periods or more. In this case, the primary loss mechanism is scattering at the defect. It is possible to increase the Q-factor even more by carefully designing the size of the defect to reduce the out-of-plane scattering by cancelling out different radiation fields with opposing signs [16]. This requires very low tolerances on the exact defect size, which is not realistic given the current state of the art processing. In this work we will not try to optimize the Q-factor further.

3.3. Defect resonators used as resonant mirrors

Figure 6a shows a typical reflection and transmission spectrum for a resonant mirror with a defect cavity. The grating has 60 periods and the dimensions are as shown in the inset of figure 5. The III-V waveguide is identical to the one in section 2 and the bonding layer thickness is 300 nm . This structure is similar to the band-edge resonant mirror in figure 3 except for the quarter-wave shift in the silicon grating. The reflection and transmission spectra also seem similar: in both cases, the maximum reflectivity is around 80% and no light is transmitted through the III-V waveguide. But there are subtle differences between both configurations. The maximum reflectivity is at a shorter wavelength, corresponding to the center instead of the edge of the band-gap in figure 2a. Even though the bonding layer thickness and the grating length are the same, the reflection bandwidth

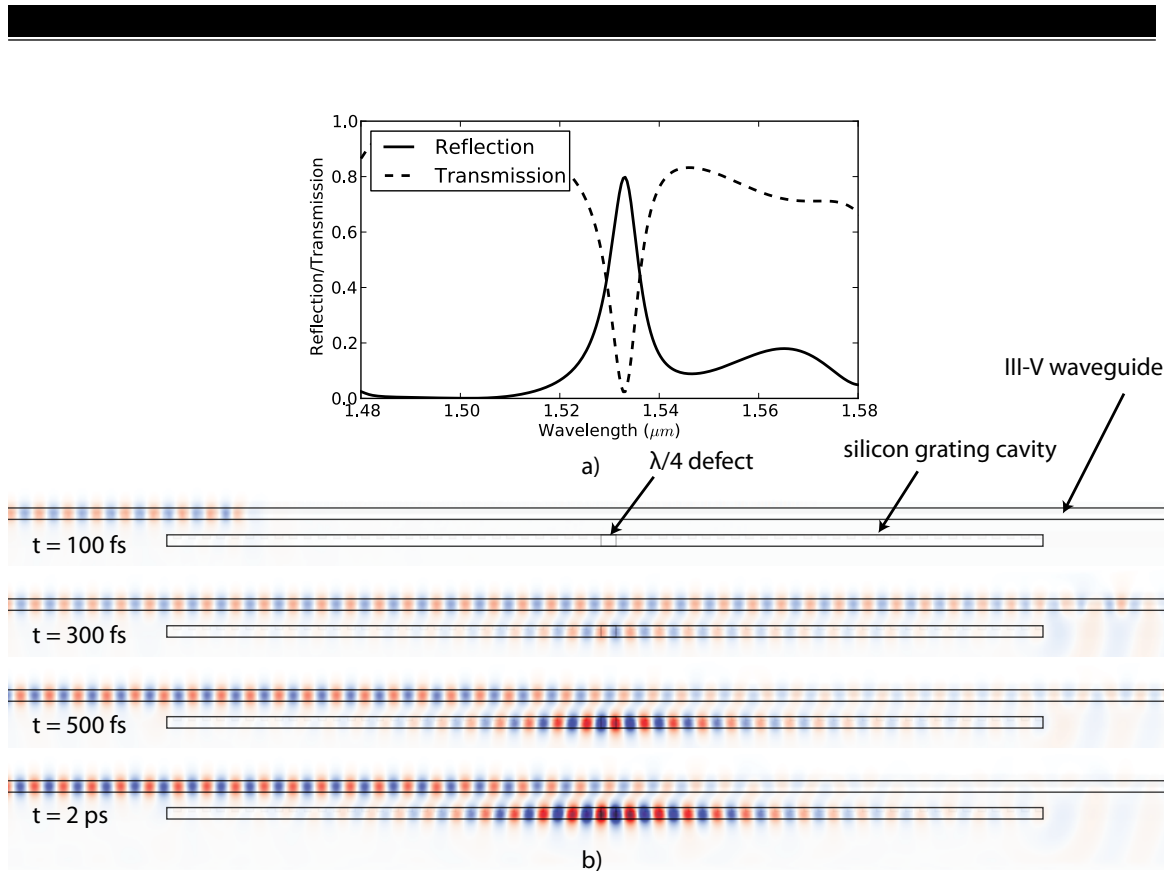


Fig. 6. a) Typical spectrum for resonant mirror with defect cavity. This particular example is for a 60 period grating with a defect in the center. The grating pitch is 285 nm and the bonding layer thickness is 300 nm. b) Field profiles at different points in time for CW injection at the cavity resonance wavelength.

of the defect resonant mirror is half (7 nm) the reflection bandwidth of the corresponding band-edge resonant mirror (14 nm). The reason for this is that the field profile of the defect resonance is not spread out along the length of the grating but is localized around the quarter-wave defect. Consequently the interaction length between the traveling mode in the III-V waveguide and the resonance mode in the silicon grating is shorter, reducing the coupling between both.

Figure 6b shows the electric field in a cross-section similar to figure 1 at different points in time. The cavity dynamics are slower than the dynamics of the band-edge cavity, which was already indicated by the narrower line width. The figure also shows that the resonance mode is localised around the defect, resulting in a shorter interaction length with the propagating mode in the III-V waveguide.

Similar to the treatment on band-edge resonators, the next two paragraphs will deal with the influence of the grating length and bonding layer thickness on the reflection spectrum of the defect-based resonant mirror.

3.3.1. Influence of grating length

In figure 7a, the reflection and transmission spectra for different grating lengths are depicted. Again, N is the total number of grating periods. The device parameters are similar to the resonant mirror in figure 6 except for the number of periods in the silicon grating. As stated before, the field profile of the silicon cavity-mode is localized around the quarter-wave defect. Consequently, its shape and spatial extent, hence the interaction length with the III-V waveguide mode, is only weakly dependent on the number of periods in the grating. Therefore, the coupling between the III-V waveguide and the silicon cavity can be considered independent of the number of periods in the grating. This is also indicated by the fact that the structure is always close to critical coupling

(no transmission through III-V waveguide), regardless of the number of periods in the grating. If the silicon cavity is critically coupled to the III-V waveguide, the maximum reflectivity is mainly determined by the Q-factor of the cavity and varies from 50% for $N = 40$ periods to 88 % for $N = 100$ periods.

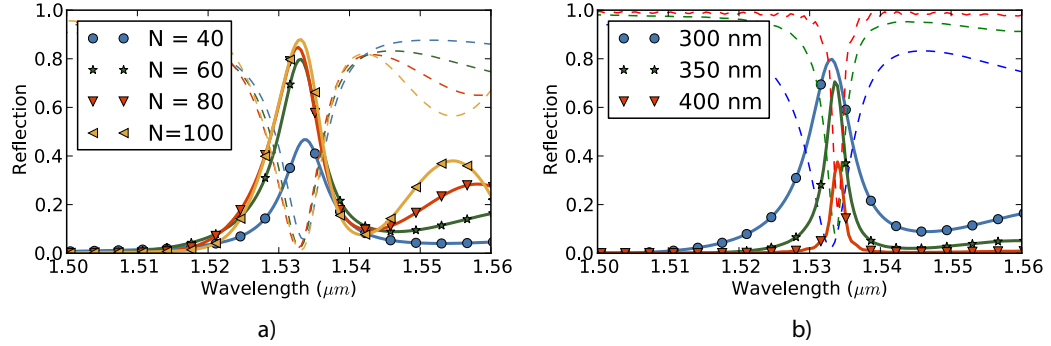


Fig. 7. Influence of the number of periods (a) and BCB thickness (b) on the reflection spectrum of a defect cavity resonant mirror. Except for the varied parameter, the structure is identical to the one presented in figure 6. Solid lines are reflection spectra, dashed lines are transmission spectra

3.3.2. Influence of bonding layer thickness

Figure 7b shows the reflection and transmission spectra for the defect resonant mirror in figure 6 for 3 different values of the bonding layer thickness. This graph is similar to figure 4b. By increasing the bonding layer thickness, the coupling between the III-V waveguide and the silicon cavity is decreased. Consequently the maximum reflectivity decreases and the reflection bandwidth becomes narrower.

4. Laser properties

To design a laser using the resonant mirrors described in the previous sections, the only parameter left to decide is the distance between the two mirrors. In between the two mirror sections the light is fully confined to the III-V waveguide as shown in figure 1. The choice of the length of this III-V waveguide between the two mirror sections is important because it will determine the spectral properties (side-mode suppression ratio - SMSR) and threshold power of the laser.

Figure 8a shows the different longitudinal resonances for a resonant mirror laser with the defect-based grating mirror of figure 6 and a mirror spacing L of $10 \mu m$, $20 \mu m$, $50 \mu m$ and $100 \mu m$. The dashed line is the reflection spectrum of the mirror (same as in figure 6a). The solid lines indicate the different resonances of the laser structure. The resonance wavelengths are calculated by considering the phase shift of the resonant mirror and the phase accumulated when propagating through the III-V waveguide. The length of each laser is slightly adjusted to align the peak of the resonant mirror's reflection spectrum to one of the longitudinal resonances. The amplitude of each bar in figure 8a is the modal gain g_{th} (in cm^{-1}) required in the III-V waveguide to reach lasing threshold. The modal threshold gain is calculated by assuming no internal losses in the III-V waveguide, so: $g_{th} = \ln(R^2)/2L_{tot}$. L_{tot} is the total length the light travels in the III-V waveguide. To a good approximation this is the distance between the two defects in the silicon cavities, so $L_{tot} \approx L + 17 \mu m$, because each silicon grating is about $17 \mu m$ long and the defect is in the center of the grating. Figure 8b shows the electric field distribution through a cross-section of a device with $L = 20 \mu m$. The figure also shows how L and L_{tot} are defined.

If the modal threshold gain g_{th} is known, the most important laser properties can be calculated

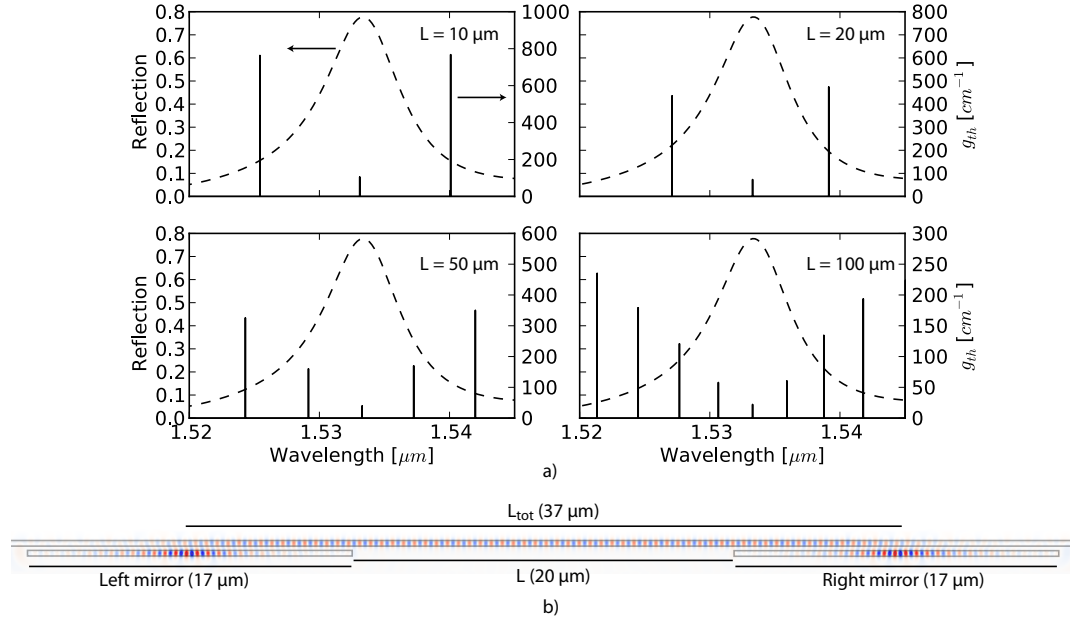


Fig. 8. a) Resonances of the laser structure for different values of the spacing L between the resonant mirror structures. The dashed curve is the reflection spectrum of the resonant mirror that is used (identical to figure 6). The height of each bar representing a laser-resonance is the modal gain required to reach threshold for that particular resonance. b) Field distribution of the resonant laser mode with the lowest threshold gain for a $20 \mu\text{m}$ spacing between the resonant mirrors.

by considering the differential equation describing the time evolution of the carrier density $N(t)$ in the laser's active region:

$$\frac{dN(t)}{dt} = \frac{P(t)}{h\nu_p V_a} - AN(t) - BN^2(t) - CN^3(t) - v_g G(N)S(t) \quad (1)$$

In this equation, $P(t)$ is the pump power absorbed in the active region, h is the Planck constant, ν_p is the frequency of the pump beam, V_a is the volume of the active region, A is the Shockley-Read-Hall recombination coefficient, B is the spontaneous recombination coefficient, C is the Auger-recombination coefficient, v_g is the group velocity of the fundamental mode in the III-V waveguide, $G(N)$ is the carrier-dependent material gain and $S(t)$ is the cavity's photon density. Assuming a bulk InGaAsP active layer the material gain in the active layer depends linearly on the carrier density:

$$G(N) = G_0(N - N_0) \quad (2)$$

With G_0 the differential gain and N_0 the transparency carrier density. The modal gain g is related to the material gain G by the confinement factor Γ of the fundamental eigenmode of the III-V waveguide: $g = \Gamma G$. With this relationship, the carrier density N_{th} required to reach threshold can be calculated using equation 2. Next, the threshold pump power P_{th} is calculated by setting dN/dt and S to zero, assuming $N = N_{th}$ and solving equation 1 for P .

The photon density S in the III-V waveguide is:

$$S = \frac{P - P_{th}}{h\nu_p v_g G_{th} V_a} \quad (3)$$

TABLE I
PARAMETERS IN RATE-EQUATION MODEL

Symbol	Parameter	Value	Reference
A	SRH-recombination coefficient	10^8 s^{-1}	[19]
B	spontaneous recombination coefficient	$2 \times 10^{-10} \text{ cm}^3 \text{ s}^{-1}$	[19]
C	Auger recombination coefficient	$1.63 \times 10^{-28} \text{ cm}^6 \text{ s}^{-1}$	[19]
v_g	III-V waveguide group velocity	10^8 m s^{-1}	simulation
G_0	differential gain (dG/dN)	$3.13 \times 10^{-16} \text{ cm}^2$	[20]
N_0	Transparency carrier density	$6.5 \times 10^{17} \text{ cm}^{-3}$	[20]
Γ	III-V waveguide confinement factor	43.3%	simulation
ν_p	frequency of pump beam	$c/1.0 \mu\text{m}$	
ν_l	output frequency of laser	$c/1.55 \mu\text{m}$	
η	transmission to SOI waveguide	15%	simulation
n_{sp}	spontaneous emission factor	2	[17]

Consequently the laser output power P_{out} is:

$$P_{out} = \eta h \nu_l \frac{V_a}{\Gamma} \frac{v_g}{2L_{tot}} S = \eta \frac{\nu_l}{\nu_p} \frac{P - P_{th}}{2L_{tot} g_{th}} \quad (4)$$

With η the fraction of the mirror's incident power that is coupled into the silicon output waveguide and ν_l the laser frequency. The side-mode suppression ratio can be calculated using [17]:

$$SMSR = \frac{\Delta g_{th}}{g_{th}} \frac{V_a}{\Gamma n_{sp}} S \quad (5)$$

with n_{sp} the spontaneous emission factor and Δg_{th} the difference in modal threshold gain between the main laser mode and the strongest side-mode. Table II shows these laser properties for the different lengths L between the mirrors. The parameters used in the calculations are in table I. The values for the different laser properties do not vary significantly for the different values of L . A spacing of $20 \mu\text{m}$ between the mirrors yields the lowest threshold power. For shorter devices, the threshold gain rises quickly. For longer devices the threshold gain is low, but the volume of the active region V_a is large, requiring a large amount of free carriers. The calculated side-mode suppression ratio is very high, around 40 dB in all cases (for $P = 2P_{th}$). These calculations correspond well to our recent experimental results [18] where we demonstrated a resonant mirror laser with mirrors identical to the ones used in this simulation and a mirror spacing of $20 \mu\text{m}$. For these devices we found a threshold power of 0.6 mW (we estimate 10% of 6 mW incident pump power is absorbed by InGaAsP layer) and a SMSR of 39 dB.

In calculating the values in table II, one of the longitudinal resonances was aligned to the maximum of the mirror's reflection spectrum. In reality, small changes in the effective index of the III-V waveguide will shift the longitudinal resonance wavelength away from the maximum reflectivity and alter the laser properties. Figure 9 shows how the threshold power P_{th} and SMSR change when the effective index of the III-V waveguide shifts with an amount Δn . Using an optical mode solver, the changes in Δn can be related to changes in width ($\Delta n/\Delta W = 0.01/200 \text{ nm}$), height ($\Delta n/\Delta H = 0.029/10 \text{ nm}$) and temperature ($\Delta n/\Delta T = 0.024/100 \text{ K}$ [21]) of the III-V waveguide. The laser wavelength shifts at $\Delta \lambda/\Delta n = 5 \text{ nm}/0.04$.

Figure 9 shows that for the shorter distance between the resonant mirrors, a significant advantage in terms of stability towards changes in the effective index is obtained. Lasers with a spacing between the mirrors of $20 \mu\text{m}$ or less can easily accommodate a Δn offset of 0.01, which corresponds to a 10% margin on the waveguide width or a 50 K rise in temperature. As can be expected from a thin-film device, all configurations are very sensitive to changes in the thickness

TABLE II
CALCULATED LASER PROPERTIES

L [μm]	P_{th} [μW]	P_{out} [μW] ($P = 2P_{th}$)	SMSR [dB]
10	623.	51.8	39.8
20	592.	49.3	40.2
50	658.	55.2	41.4
100	872.	72.8	42.4

of the III-V waveguide, but this can be controlled very accurately using epitaxial growth.

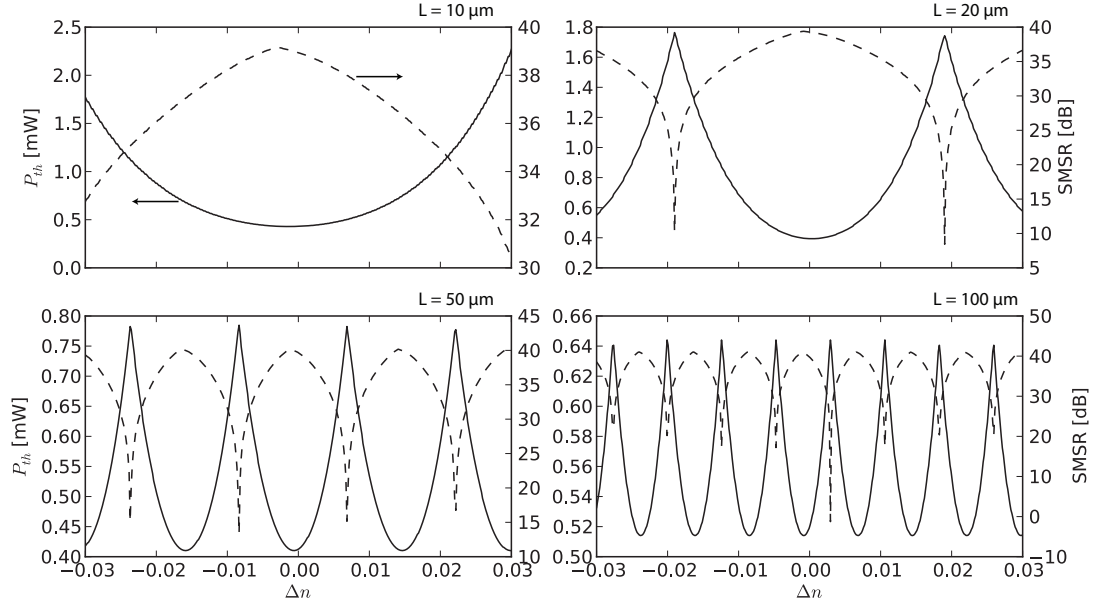


Fig. 9. Threshold power (solid line) and SMSR (dashed line) for changes in n_{eff} for different values of the spacing between the resonant mirrors. Changes in Δn can be related to changes in width ($\Delta n/\Delta W = 0.01/200nm$), height ($\Delta n/\Delta H = 0.029/10nm$) and temperature ($\Delta n/\Delta T = 0.024/100K$) of the III-V waveguide.

According to the previous discussion, the ideal spacing between the two silicon mirrors is between $10 \mu m$ and $20 \mu m$ for this particular case. For shorter devices, the gain necessary to reach threshold will increase and the required carrier density will be too high. Longer devices are too sensitive to variations in the effective index of the III-V waveguide, which can result in multi-mode lasing and unpredictable behavior.

5. Conclusion

In this article we have presented a novel approach to heterogeneously integrated III-V on silicon micro-lasers, based on the concept of resonant mirrors. We have studied the behavior of such mirrors in two different configurations: using a band-edge grating resonator and a defect grating resonator. In both cases we investigated how the characteristics of the reflection and transmission spectrum changed when the values of the most important parameters were varied. Using the mirror characteristics, the threshold power and side-mode suppression ratio were estimated to $600 \mu W$ and $40 dB$ respectively. Recent experimental results are in good agreement to these calculations.

This work paves the way to the realisation of large arrays of single-mode micro-lasers co-integrated on a silicon chip, with a well controlled lasing wavelength and wavelength spacing. This can be of particular interest for WDM applications or as a source for spectroscopic sensing systems.

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